TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC7MH257FK

Quad 2-Channel Multiplexer (3-State)

The TC7MH257FK is an advanced high speed CMOS multiplexer fabricated with silicon gate ${\rm C^2MOS}$ technology.

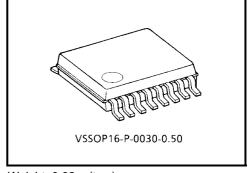
It achieves the high speed operation similar to equivalent bipolar schottky TTL while maintaining the CMOS low power dissipation.

It is composed of four independent 2-channel multiplexers with common SELECT and $\overline{OUTPUTENABLE}$ (\overline{OE}).

If \overline{OE} is set low, the outputs are held in a high-impedance state. When SELECT is set low, "A" data inputs are enabled.

Conversely, when SELECT is high, "B" data inputs are enabled.

An input protection circuit ensures that 0 to 7 V can be applied to the input pins without regard to the supply voltage. This device can be used to interface 5 V to 3 V systems and two supply



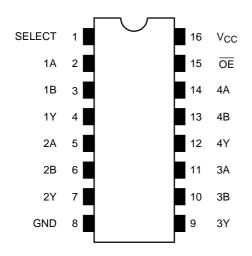
Weight: 0.02 g (typ.)

systems such as battery back up. This circuit prevents device destruction due to mismatched supply and input voltages.

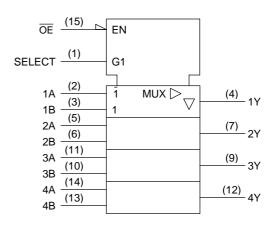
Features

- High speed: $t_{pd} = 3.6 \text{ ns (typ.)} (V_{CC} = 5 \text{ V})$
- Low power dissipation: $I_{CC} = 4 \mu A \text{ (max) (Ta} = 25 ^{\circ}\text{C)}$
- High noise immunity: V_{NIH} = V_{NIL} = 28% V_{CC} (min)
- Power down protection is provided on all inputs.
- Balanced propagation delays: $t_pLH \approx t_pHL$
- Wide operating voltage range: $V_{CC (opr)} = 2 \sim 5.5 \text{ V}$
- Low noise: VOLP = 0.8 V (max)
- Pin and function compatible with 74ALS257

Pin Assignment (top view)



IEC Logic Symbol



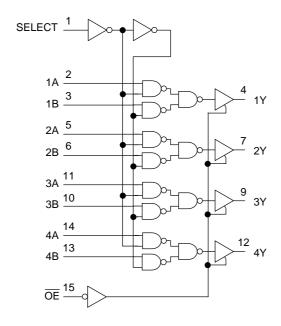
Truth Table

	Outputs				
ŌĒ	Select	- Outputs			
Н	Х	Х	Х	Z	
L	L	L	Х	L	
L	L	Н	Х	Н	
L	Н	Х	L	L	
L	Н	Х	Н	Н	

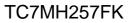
X: Don't care

Z: High impedance

System Diagram



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Maximum Ratings

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Characteristics	Symbol	Rating	Unit
Supply voltage range	V _{CC}	-0.5~7.0	V
DC input voltage	V _{IN}	-0.5~7.0	V
DC output voltage	Vout	-0.5~V _{CC} + 0.5	V
Input diode current	I _{IK}	-20	mA
Output diode current	I _{OK}	±20	mA
DC output current	I _{OUT}	±25	mA
DC V _{CC} /ground current	Icc	±50	mA
Power dissipation	P _D	180	mW
Storage temperature	T _{stg}	-65~150	°C

Recommended Operating Conditions

Characteristics	Symbol	Rating	Unit	
Supply voltage	pply voltage V _{CC} 2.0-		V	
Input voltage	V _{IN}	0~5.5	V	
Output voltage	V _{OUT}	0~V _{CC}	V	
Operating temperature	T _{opr}	-40~85	°C	
Input rise and fall time	dt/dv	$0 \sim 100 \text{ (V}_{CC} = 3.3 \pm 0.3 \text{ V)}$	ns/V	
input noe and fail time	ui/uv	$0 \sim 20 \ (V_{CC} = 5 \pm 0.5 \ V)$	113/ V	

Electrical Characteristics

DC Characteristics

Characteristics		Symbol Test Condition			Ta = 25°C			Ta = -40~85°C		- Unit	
		Symbol	rest	lest Condition		Min	Тур.	Max	Min	Max	Unit
High Input voltage			_		2.0	1.50	_	_	1.50	_	
	High level	V _{IH}			3.0~5.5	V _{CC} × 0.7	_	_	V _{CC} × 0.7	_	V
input voltage							_	0.50	_	0.50	V
	Low level	V_{IL}	_		3.0~5.5		_	V _{CC} × 0.3	_	V _{CC} × 0.3	
				Ι _{ΟΗ} = -50 μΑ	2.0	1.9	2.0		1.9	_	
	High level	Vон	V _{IN} = V _{IH} or V _{IL}		3.0	2.9	3.0		2.9	_	
Output voltage					4.5	4.4	4.5	_	4.4	_	V
				$I_{OH} = -4 \text{ mA}$	3.0	2.58	_	_	2.48	—	
				$I_{OH} = -8 \text{ mA}$	4.5	3.94	_	_	3.80	—	
Output voltage	Low level	V _{OL}	V _{IN} = V _{IH} or V _{IL}	I _{OL} = 50 μA	2.0	_	0	0.1	_	0.1	
					3.0	_	0	0.1	_	0.1	
					4.5	_	0	0.1	_	0.1	
				$I_{OL} = 4 \text{ mA}$	3.0	_	_	0.36	_	0.44	
				$I_{OL} = 8 \text{ mA}$	4.5	_	_	0.36	_	0.44	
3-state output off-state current		l _{OZ}	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{OUT} = V_{CC} \text{ or GND}$		5.5			±0.25	_	±2.50	μΑ
Input leakage cu	rrent	I _{IN}	V _{IN} = 5.5 V or GND		0~5.5	_	_	±0.1	_	±1.0	μΑ
Quiescent supply current		Icc	V _{IN} = V _{CC} or GND		5.5	_	_	4.0	_	40.0	μΑ

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AC Characteristics (Input: $t_r = t_f = 3 \text{ ns}$)

Characteristics	Symbol	Test Condition	Toot Condition		Ta = 25°C			Ta = -4	Unit	
Characteristics	Symbol	rest Condition	V _{CC} (V)	C _L (pF)	Min	Тур.	Max	Min	Max	Offic
_	t _{pLH}		3.3 ± 0.3 -	15	_	5.8	9.3	1.0	11.0	ns
Propagation delay time				50		8.3	12.8	1.0	14.5	
(A, B-Y)	t _{pHL}		5.0 ± 0.5	15		3.6	5.9	1.0	7.0	113
			3.0 ± 0.5	50		5.1	7.9	1.0	9.0	
			3.3 ± 0.3	15		7.0	11.0	1.0	13.0	
Propagation delay time	^t pLH ^t pHL	_	3.3 ± 0.3	50		9.5	14.5	1.0	16.5	ns
(SELECT-Y)			5.0 ± 0.5	15		4.0	6.8	1.0	8.0	
				50		5.5	8.8	1.0	10.0	
	t _{pZL} t _{pZH}	$R_L = 1 \text{ k}\Omega$	3.3 ± 0.3	15		6.7	10.5	1.0	12.5	ns
3-state output enable time				50		9.2	14.0	1.0	16.0	
3-state output enable time			5.0 ± 0.5	15	_	3.6	6.8	1.0	8.0	
			3.0 ± 0.3	50	_	5.1	8.8	1.0	10.0	
2 state output disable time	t _{pLZ}	$R_L = 1 \text{ k}\Omega$	3.3 ± 0.3	50	_	8.6	12.0	1.0	13.5	ns
3-state output disable time	t _{pHZ}		5.0 ± 0.5	50		5.7	7.9	1.0	9.0	10
Input capacitance	C _{IN}	-				4	10	_	10	pF
Output capacitance	C _{OUT}	-			_	6	_	_	_	pF
Power dissipation capacitance	C _{PD}			(Note)	_	23	_	_	_	pF

Note: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

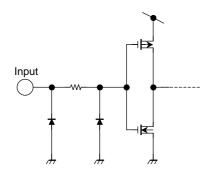
Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/4 \text{ (per bit)}$

Noise Characteristics (Input: $t_r = t_f = 3 \text{ ns}$)

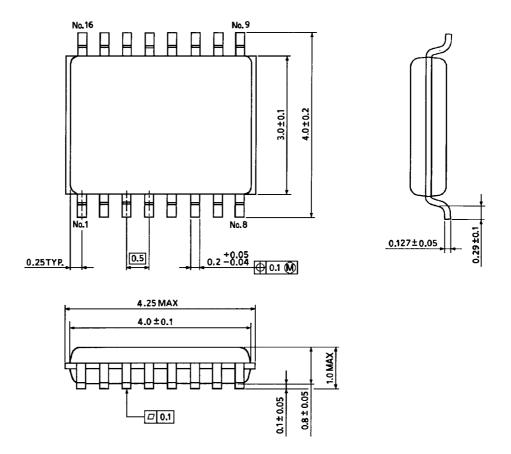
Characteristics	Symbol	Test Condition		Ta = 25°C		Unit
Characteristics	Syllibol	rest Condition	V _{CC} (V)	Тур.	Limit	Offic
Quiet output maximum dynamic V _{OL}	V _{OLP}	C _L = 50 pF	5.0	0.3	0.8	V
Quiet output minimum dynamic V _{OL}	V _{OLV}	C _L = 50 pF	5.0	-0.3	-0.8	V
Minimum high level dynamic input voltage $V_{\mbox{\scriptsize IH}}$	V _{IHD}	C _L = 50 pF	5.0	_	3.5	V
Maximum low level dynamic input voltage V_{IL}	V _{ILD}	C _L = 50 pF	5.0	_	1.5	V

Input Equivalent Circuit



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Package Dimensions



Weight: 0.02 g (typ.)

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